

Silicon NPN Power Transistors

2SD478

DESCRIPTION

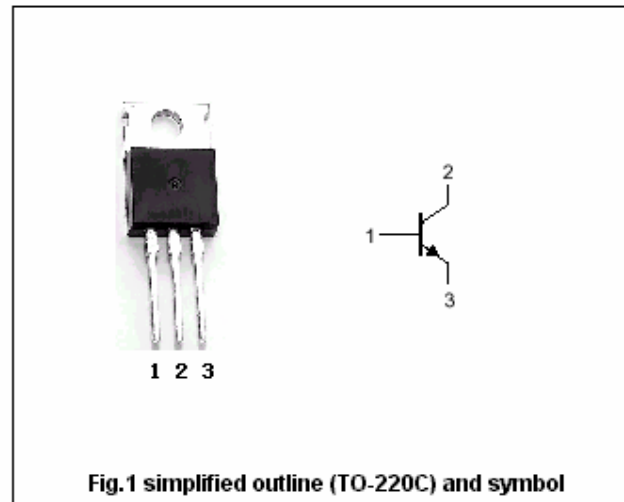
- With TO-220C package
- Complement to type 2SB568

APPLICATIONS

- Low frequency high voltage power amplifier TV vertical deflection output

PINNING

PIN	DESCRIPTION
1	Base
2	Collector; connected to mounting base
3	Emitter

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	200	V
V_{CEO}	Collector-emitter voltage	Open base	150	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		2	A
I_{CM}	Collector current-peak		5	A
P_C	Collector power dissipation	$T_a=25$	1.8	W
		$T_C=25$	30	
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-45~150	

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CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=50mA$; $R_{BE}=\infty$	150			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=5mA$; $I_C=0$	6			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=0.5A$; $I_B=50mA$			3.0	V
V_{BE}	Base-emitter voltage	$I_C=50mA$; $V_{CE}=4V$			1.0	V
I_{CBO}	Collector cut-off current	$V_{CB}=120V$; $I_E=0$			1.0	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=4V$; $I_C=0$			1.0	μA
h_{FE-1}	DC current gain	$I_C=50mA$; $V_{CE}=4V$	60		320	
h_{FE-2}	DC current gain	$I_C=0.5A$; $V_{CE}=10V$	60			

◆ h_{FE-1} classifications

B	C	D
60-120	100-200	160-320

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PACKAGE OUTLINE

